

Imaging and optical properties of single core-shell GaAs-AlGaAs nanowires

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Australian Research Council

Motivation

- we study electronic structure and optical properties of single core-shell GaAs-AlGaAs nanowires

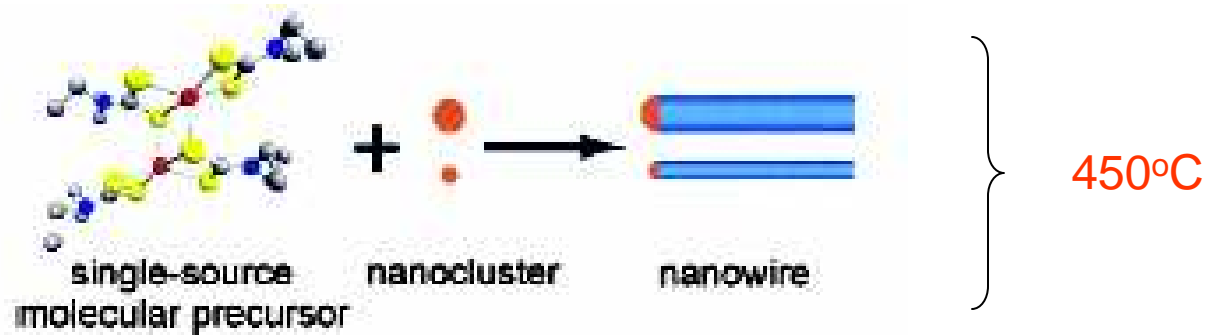
bare GaAs nanowires: low quantum efficiency due to nonradiative surface recombination

- core-shell GaAs-AlGaAs nanowires have much higher quantum efficiency

Sample growth

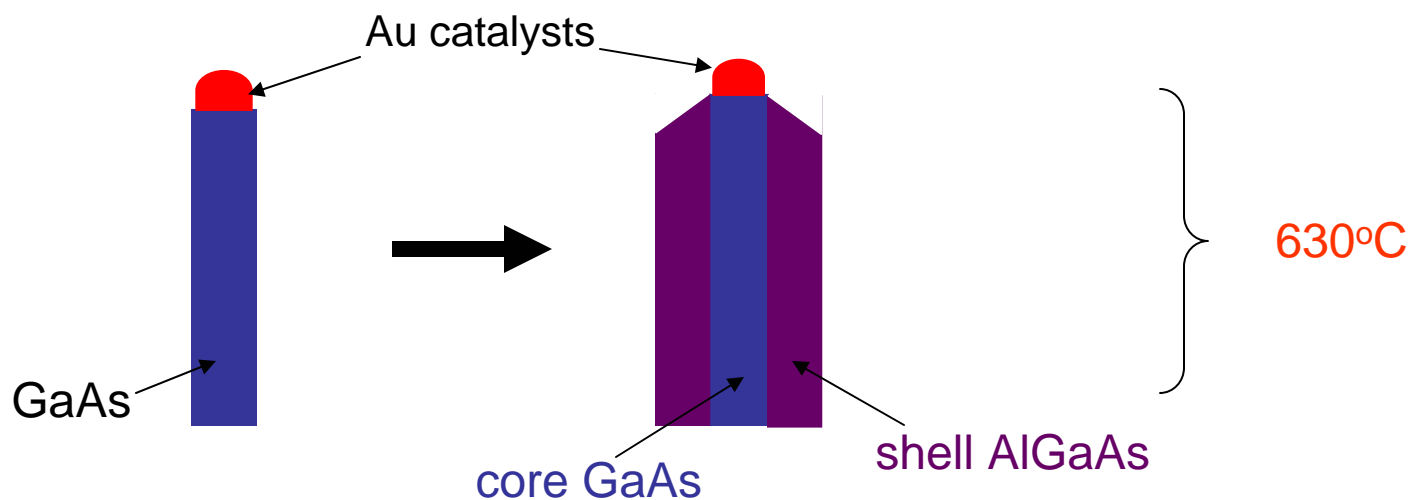
Grown by Vapor-Liquid-Solid technique

core:

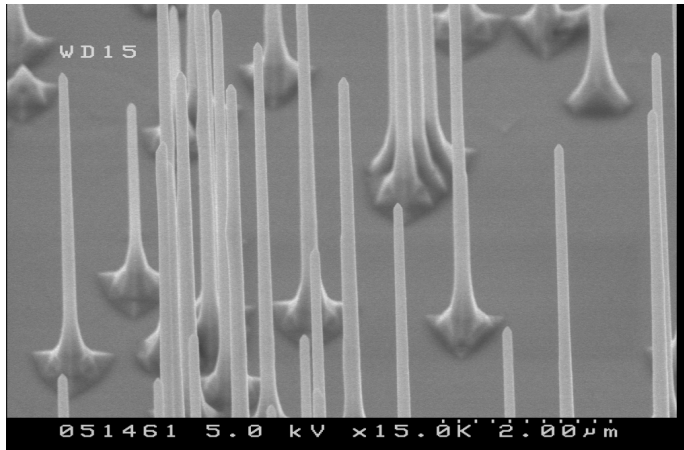


C.J. Barrelet et al, J. Am. Chem. Soc. 125, 11498 (2003)

shell:



Single nanowire studies



Field-Emission Scanning
Electron Microscope (FESEM)
image

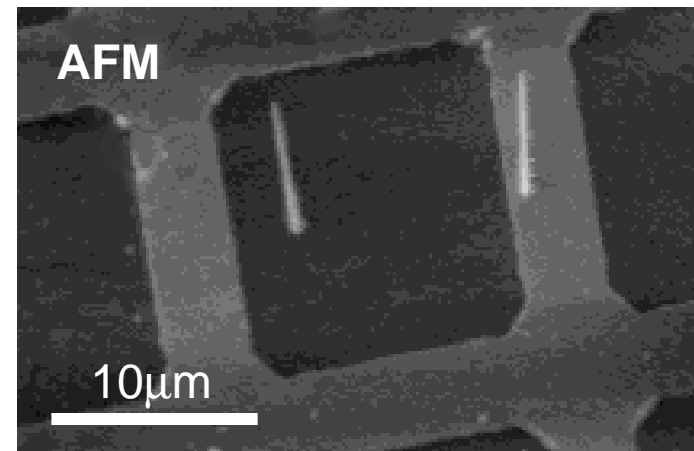
nanowires were removed from the
growth substrate into solution and
deposited onto a silicon substrate

a single nanowire:

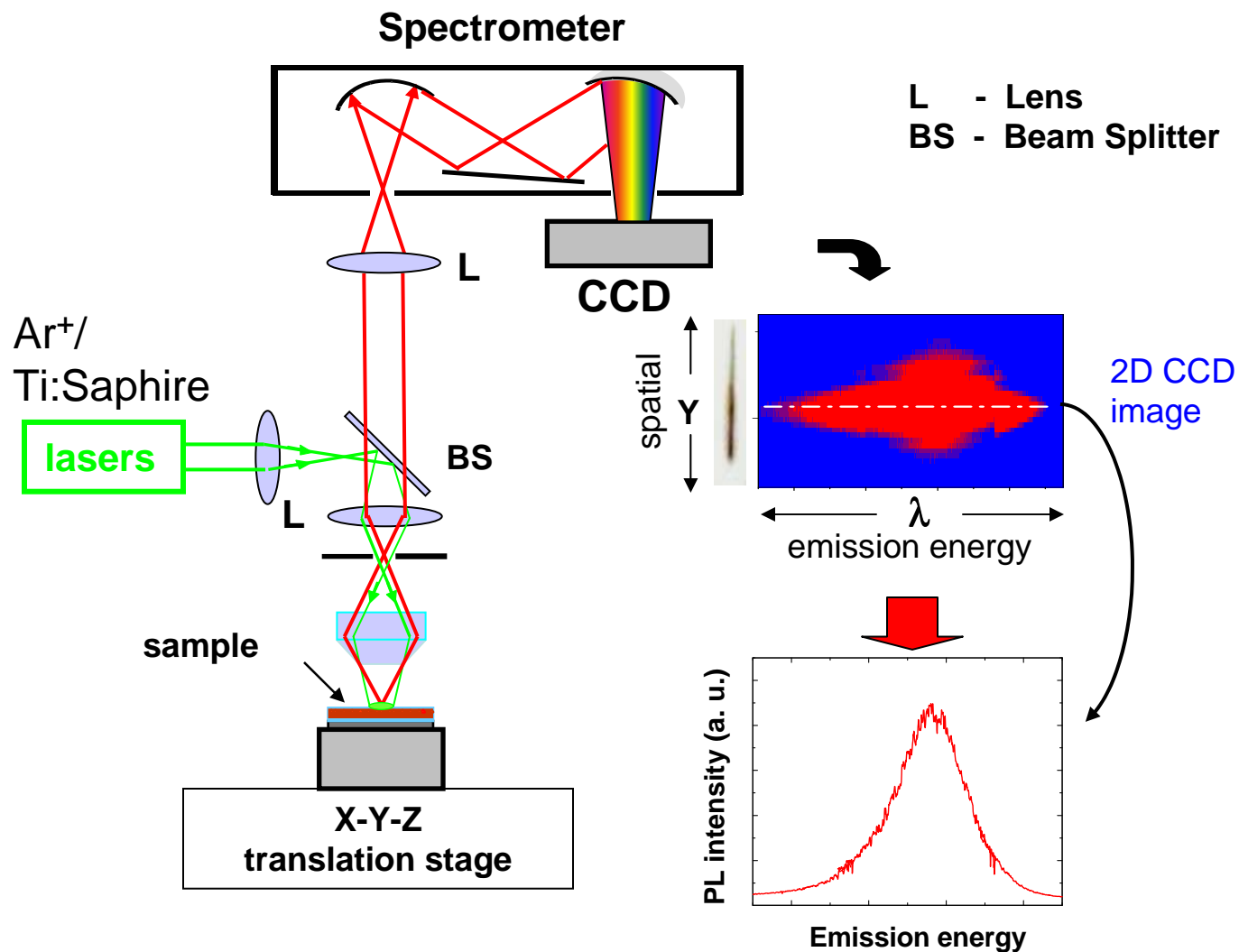
~80nm in diameter, ~5-8 μm long



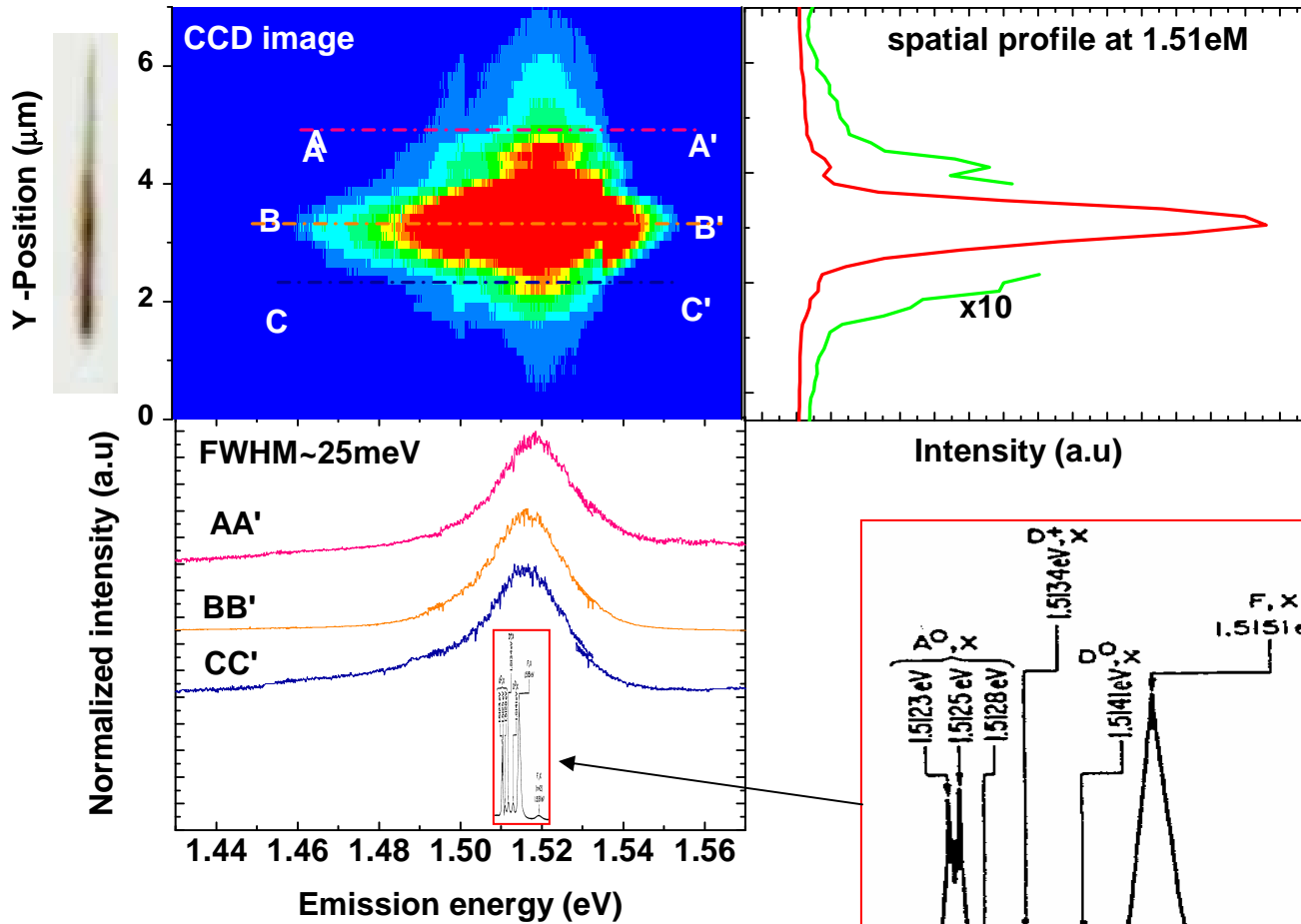
wire's diameter > Bohr exciton diameter
=> expect no quantum confinement



Experimental setup



Low-T PL imaging



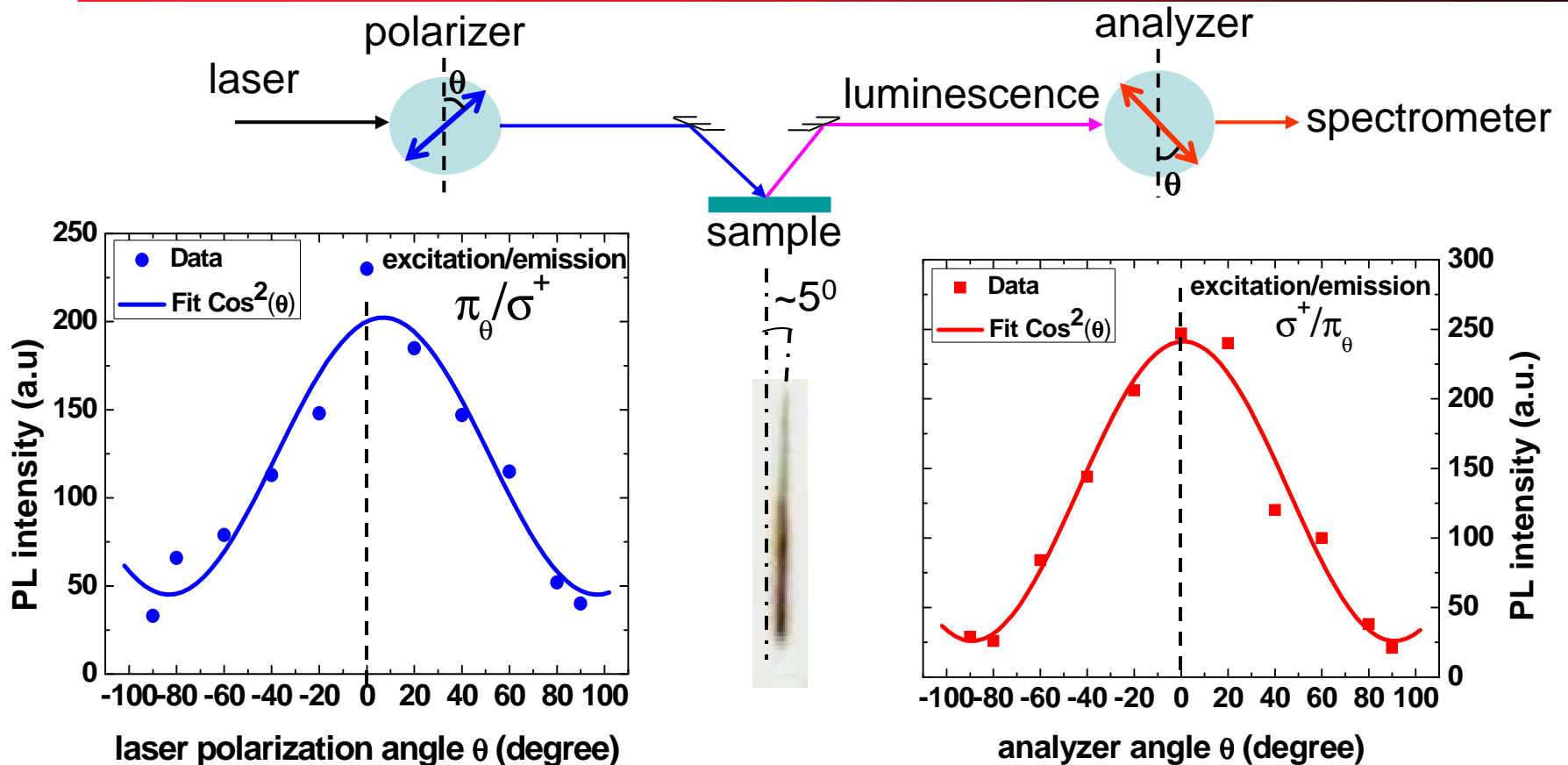
2D CCD image (spatial vs. emission) shows PL emission along the wire.

shows same emission spectra along the wire

undoped MBE-grown GaAs epilayer (PL at 5K)

(Heiblum et al. J. Vac. Sci. Tech. B2 233 (1984))

Polarization studies

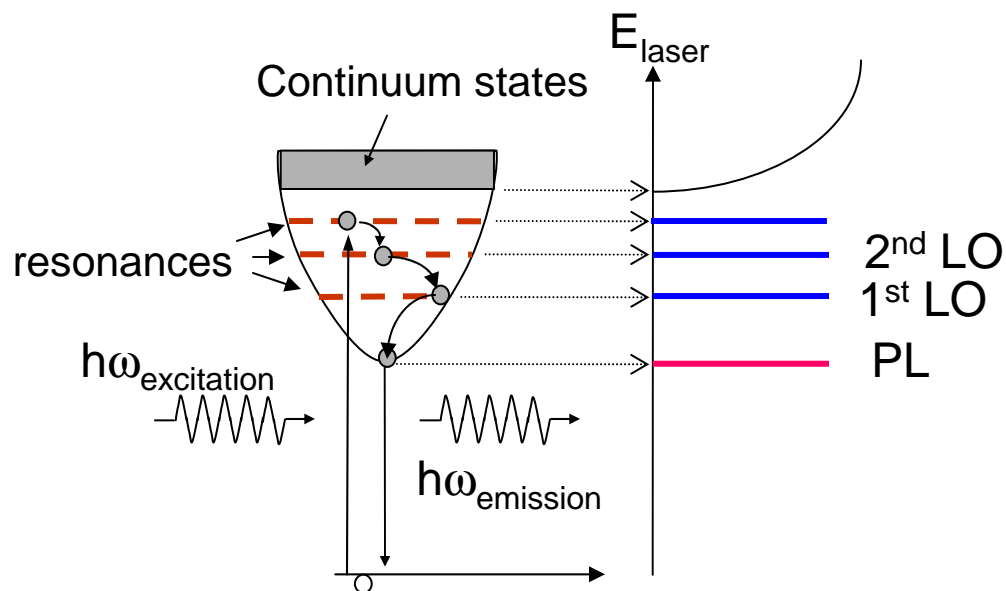


polarizer = π_{θ} ; analyzer = σ^{+}

polarizer = σ^{+} ; analyzer = π_{θ}

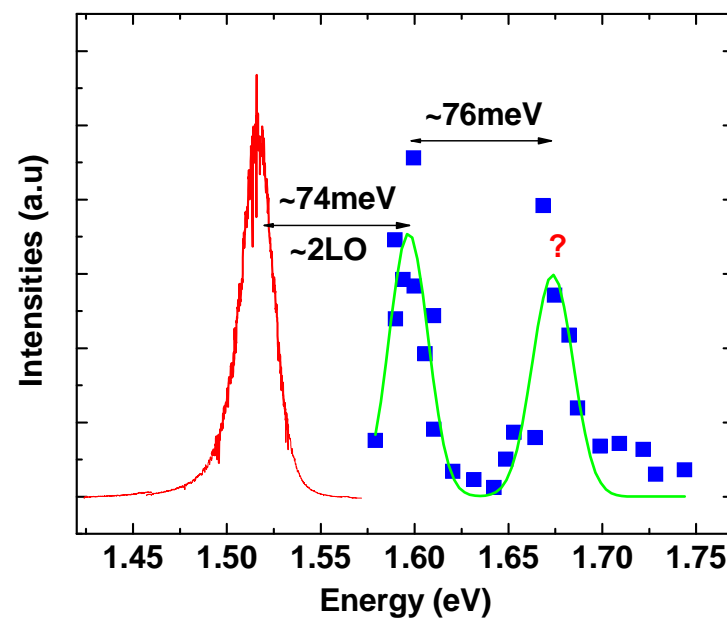
PL emission is *strongly polarized* parallel to the wire, and is *strongly enhanced* when the laser excitation is polarized parallel to the wire

Resonant excitation



tune excitation energy, E_{Laser} ,
record PL intensity

resonances at $\sim 74\text{meV}$ and 150meV
above free exciton energy



Conclusions

- core-shell GaAs-AlGaAs nanowires display strong PL emission (non-radiative surface recombination is suppressed)
- PL emission is *strongly enhanced* when the laser excitation is polarized parallel to the wire, and is *strongly polarized* parallel to the wire
- striking excitation resonances at ~ 74 meV and ~ 150 meV above the PL emission line
 - 74 meV: 2LO resonance - phonon-assisted absorption (GaAs)
 - 150 meV: LO resonance of GaAs (higher order) or AlGaAs

Dove Prism (DP) can be used to rotate image of a nanowire

